



# 3DD157(3DD158)

## NPN Silicon Low Frequency High Power Transistor



### Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

### TECHNICAL DATA:

(Ta = 25°C )

Parameter name	Symbols	Unit	Specifications						Test Condition
			A	B	C	D	E	F	
Collector-Emitter Voltage	V <sub>CEO</sub>	V	50	100	150	200	250	300	
Emitter-Base Voltage	V <sub>EBO</sub>	V	5						
Max. Collector Current	I <sub>CM</sub>	A	3.0						
Max. Collector Dissipation	P <sub>CM</sub>	W	30						Tc:75°C
Junction Temperature	T <sub>jm</sub>	°C	175						
Storage Temperature	T <sub>stg</sub>	°C	-55~+175						
Collector-Emitter Leakage Current	I <sub>CEO</sub>	mA	Max.:1.0						A:V <sub>CE</sub> =30V;B:V <sub>CE</sub> =50V; C~F:V <sub>CE</sub> =100V
Collector- Emitter Saturation Voltage Drop	V <sub>CE(sat)</sub>	V	Max.:1.0						I <sub>C</sub> =1.5A,I <sub>B</sub> =0.15A
DC Current Gain	h <sub>FE</sub>		Min.:15,Max.:180						V <sub>CE</sub> =5V,I <sub>C</sub> =1.5A
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	V	A	B	C	D	E	F	I <sub>C</sub> =3mA
			50	100	150	200	250	300	
C-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	V	80	150	200	250	350	400	I <sub>C</sub> =3mA
E-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	V	5						I <sub>E</sub> =1mA

### h<sub>FE</sub> Colored:

Color	Red	Orange	Yellow	Green	Blue	Purple
h <sub>FE</sub>	15~25	25~40	40~55	55~80	80~120	120~180

### Outline and Dimensions: